

# BCW66G

# **NPN General Purpose Amplifier**

- This device is designed for general purpose amplifier applications at collector currents to 500mA.
- Sourced from process 13.



1. Base 2. Emitter 3. Collector

# **Absolute Maximum Ratings \*** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	1	Α
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ <b>+</b> 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

  1. These ratings are based on a maximum junction temperature of 150degrees C.

  2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

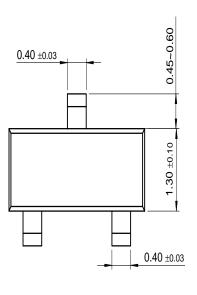
# Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

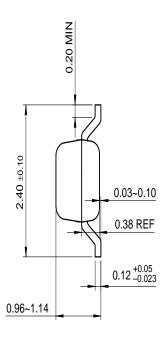
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A$	75			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA	45			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10μA	5			V
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CB</sub> = 45V, I <sub>E</sub> = 0			20	nA
		$V_{CB} = 45V, I_{E} = 0$ $T_{A} = 150^{\circ}C$			20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 4V			20	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 10V, I_{C} = 100\mu A$ $V_{CE} = 1V, I_{C} = 10mA$ $V_{CE} = 1V, I_{C} = 100mA$ $V_{CE} = 2V, I_{C} = 500mA$	50 110 160 60		400	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			0.3 0.7	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA			2	V
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 1MHz			12	pF
C <sub>ibo</sub>	Input Capacitance	V <sub>EB</sub> = 0.5V, f = 1MHz			80	pF
f <sub>T</sub>	Current gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 20mA, f = 100MHz	100			MHz
NF	Noise Figure	$V_{CE} = 5V$ , $I_{C} = 0.2$ mA, $R_{S} = 1$ k $\Omega$ , $f = 1$ KHz, BW = 200Hz			10	dB
t <sub>on</sub>	Turn-On Time	$I_{B1} = I_{B2} = 15mA$			100	ns
t <sub>off</sub>	Turn-Off Time	$I_C = 150 \text{mA}, R_L = 150 \Omega$			400	1

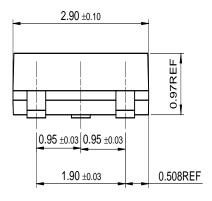
### **Thermal Characteristics** Symbol Min. Max. Units Parameter Тур. $P_{\mathsf{D}}$ 350 mW Total Device Dissipation mW/°C Derate above 25°C 2.8 °C/W 357 Thermal Resistance, Junction to Ambient $R_{\theta JA}$

# **Package Dimensions**

# **SOT-23**







Dimensions in Millimeters

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EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
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Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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